

# Combined Modeling of Electromigration, Thermal and Stress Migration in AC Interconnect Lines

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# Outline

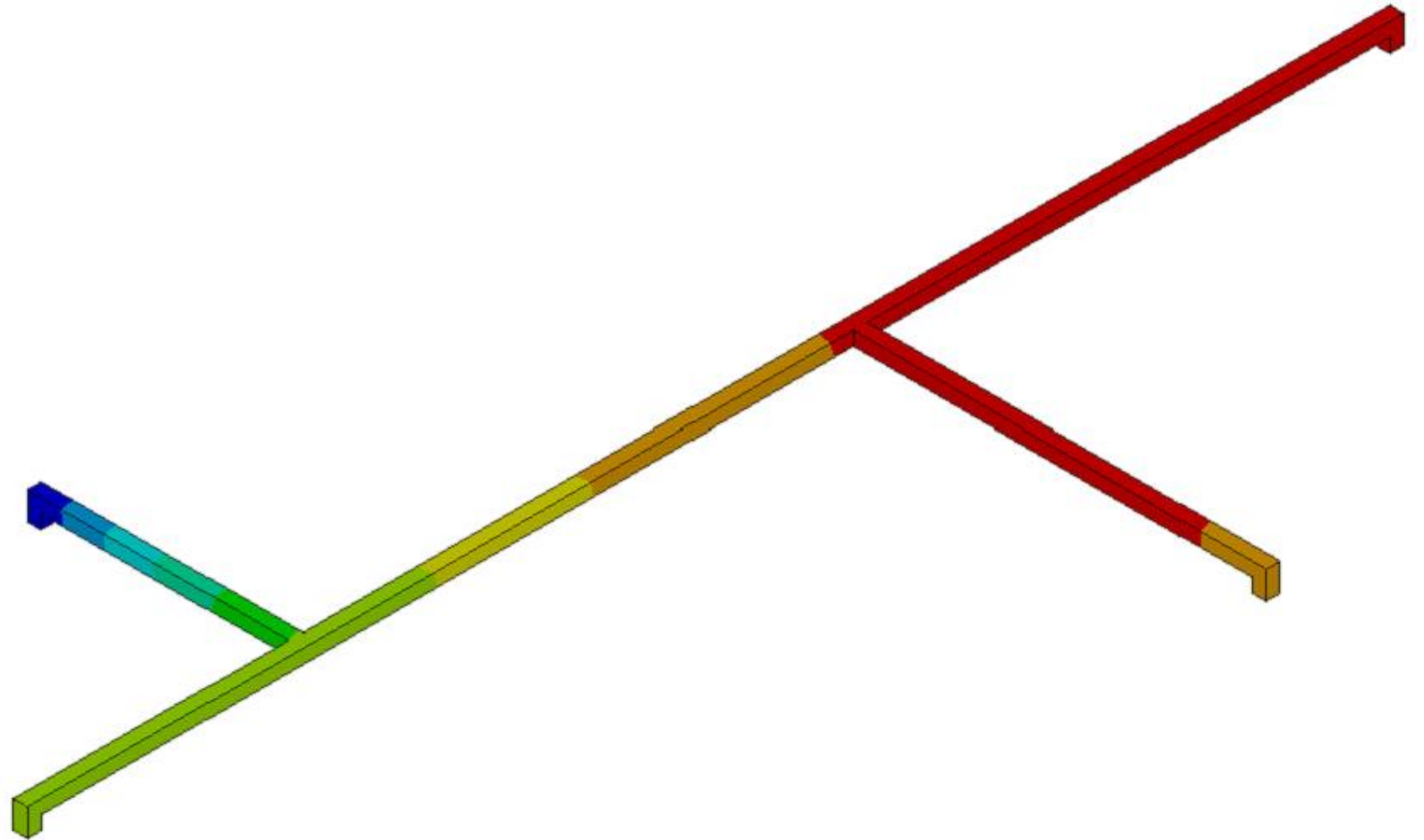
## Introduction

- Motivation
- Basics of EM, TM, and SM
- Migration in AC Nets

## Novel FEM Models

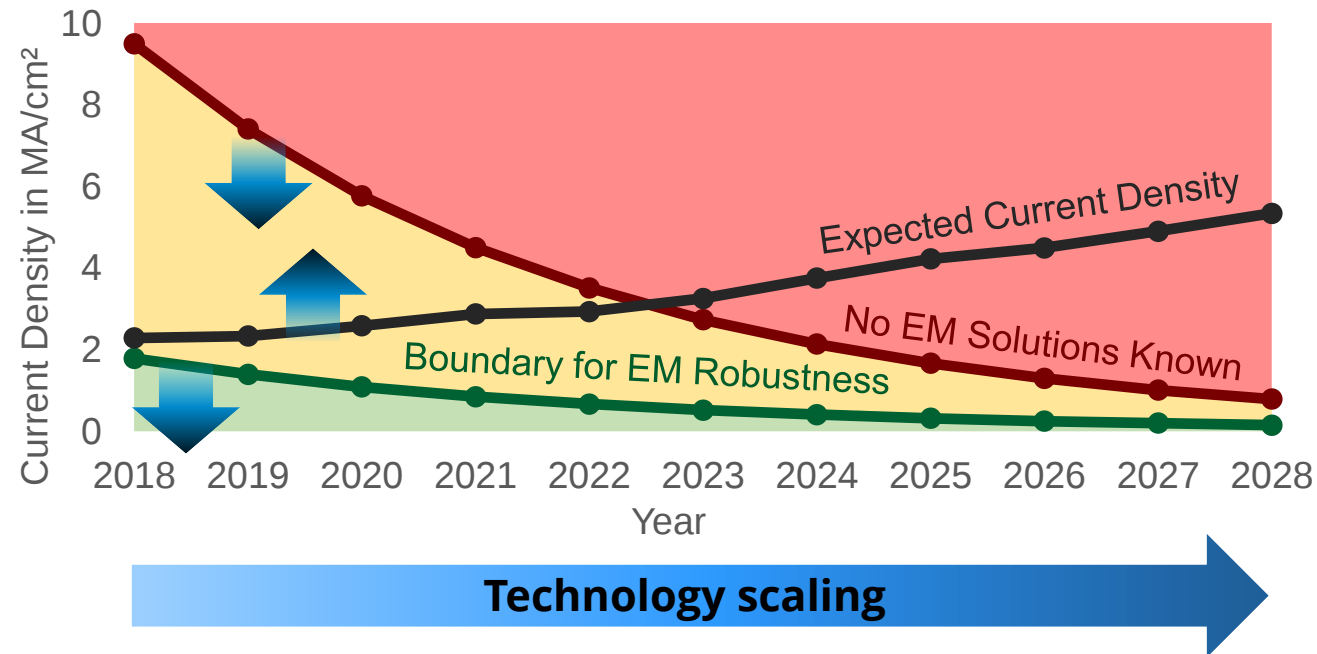
- General Concept
- Results
- Verification
- Outlook

## Summary



# Motivation

## ITRS Roadmap (2015)

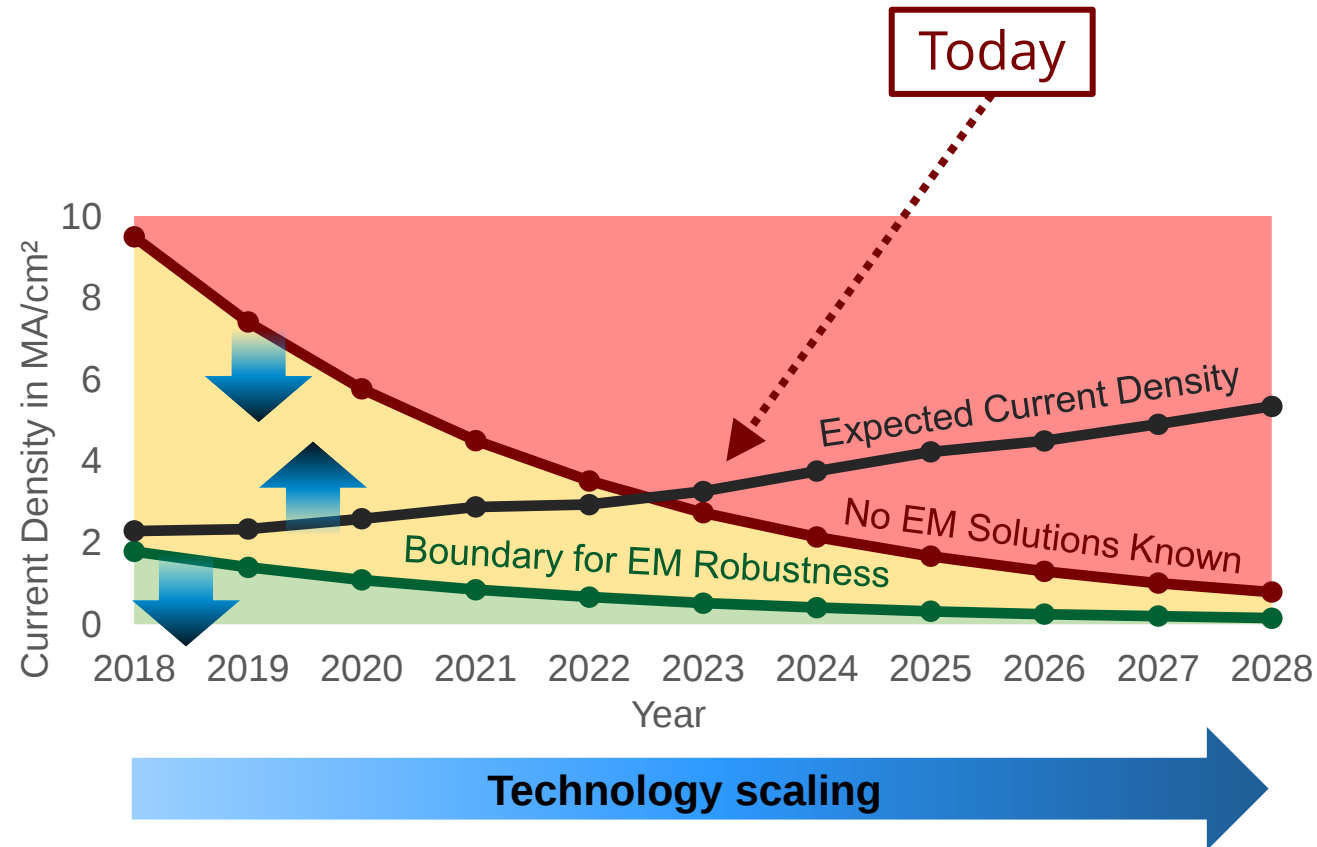


### Additional Trends:

- Rising number of nets
- Higher complexity of migration mechanisms:
  - Temperature dependency
  - Interconnect scaling → surface effects
- AC nets are increasingly affected by migration-induced degradation

# Motivation

## ITRS Roadmap (2015)

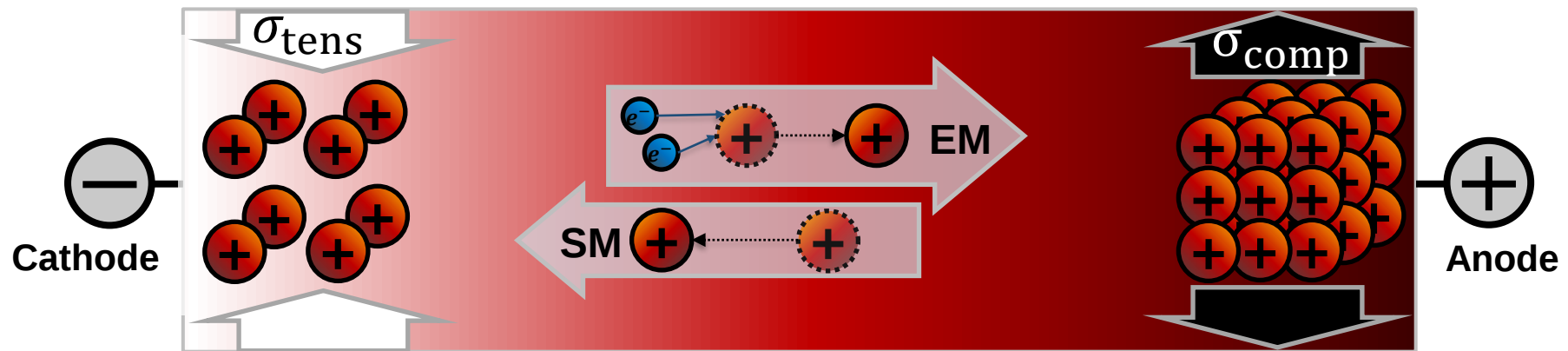


How have these issues been addressed?

- New interconnect materials
- Layout design with EM countermeasures
- Novel (stress-based) migration models → especially for PDNs

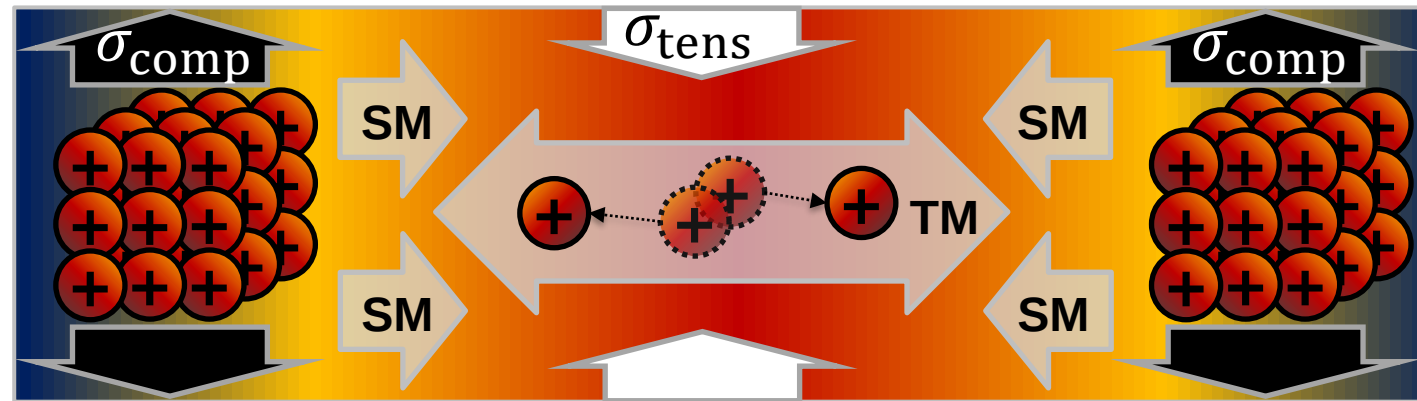
# Electromigration

- Atomic motion driven by an electric current
- Cathode: tensile stress (voids)
- Anode: compressive stress (hillocks)
- Counteracting force: stress migration (SM, driven by stress gradients)



# Thermal Migration

- Atomic motion driven by temperature gradients due to
  - Joule heating
  - Devices with high power dissipation
- Often neglected compared to EM, but gains significance



# Stress Evolution

- Combined EM, TM, and SM cause stress profile within an interconnect
- Stress evolution is described by the Korhonen equation (originally EM and SM, expanded by TM)
- Stress distribution eventually reaches a steady state (for constant current density and temperature profile)
- Minimum/maximum occurring stress: decisive parameters for migration robustness

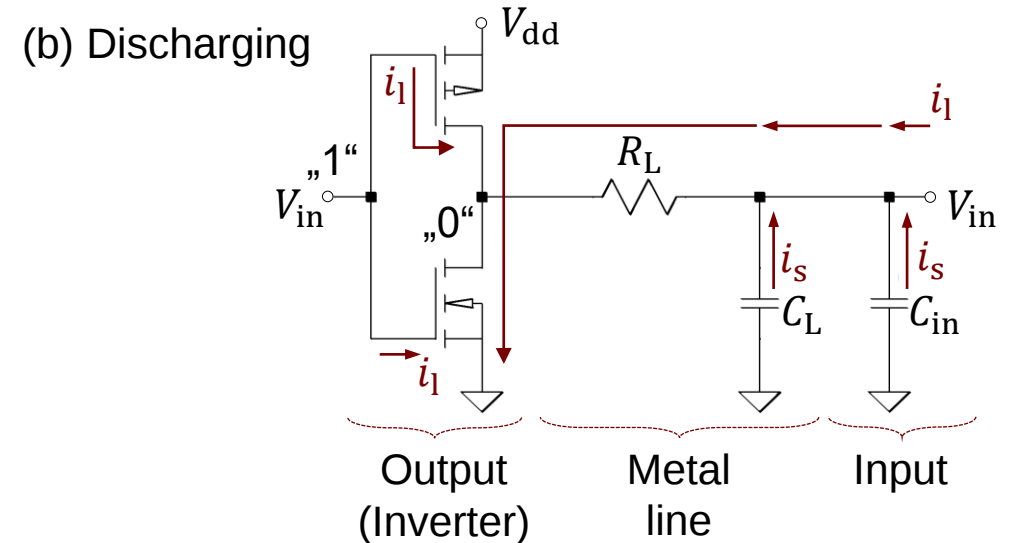
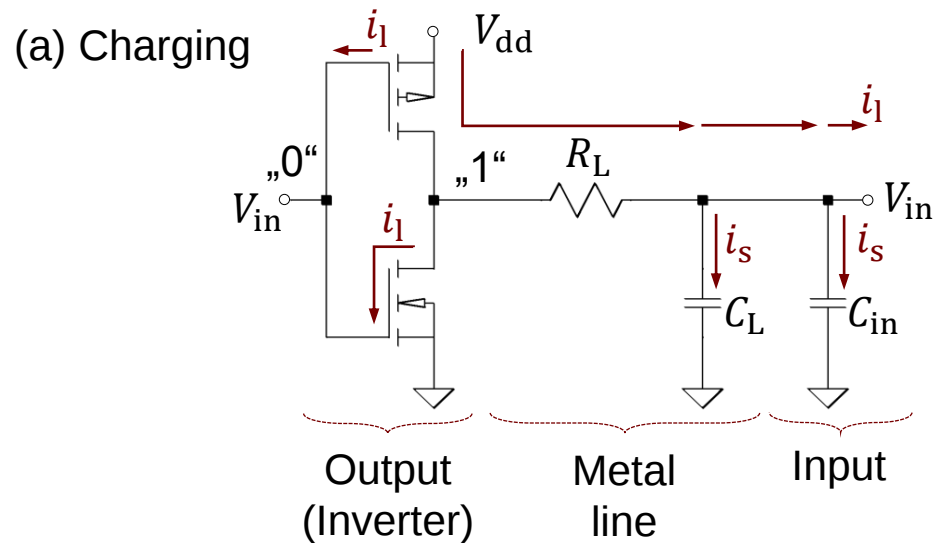
$$\frac{\partial \sigma}{\partial t} = \frac{\partial}{\partial x} \left[ \frac{DB\Omega}{k_B T} \left( \underbrace{\frac{\partial \sigma}{\partial x}}_{\text{SM}} - \underbrace{\frac{e\rho Z j}{\Omega}}_{\text{EM}} - \underbrace{\frac{Q}{\Omega T} \frac{\partial T}{\partial x}}_{\text{TM}} \right) \right]$$

# Migration in AC Nets

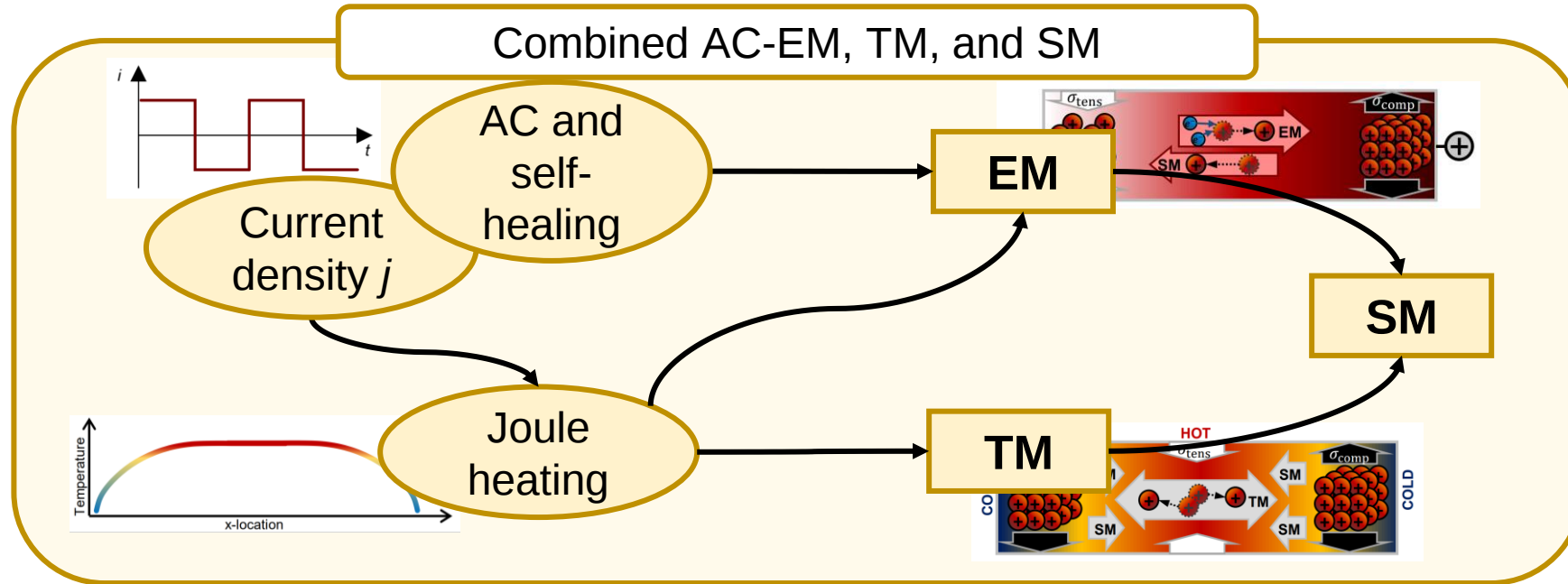
Signal lines are stressed with **alternating currents** due to

- (static) leakage power
- (dynamic) switching power

## EM: Effect of self-healing



# Migration in AC Nets



- Self-healing is imperfect and can be modeled by a factor  $r$  ( $\approx 0.7-0.9$ )
- Joule heating and TM are independent from current direction

# Outline

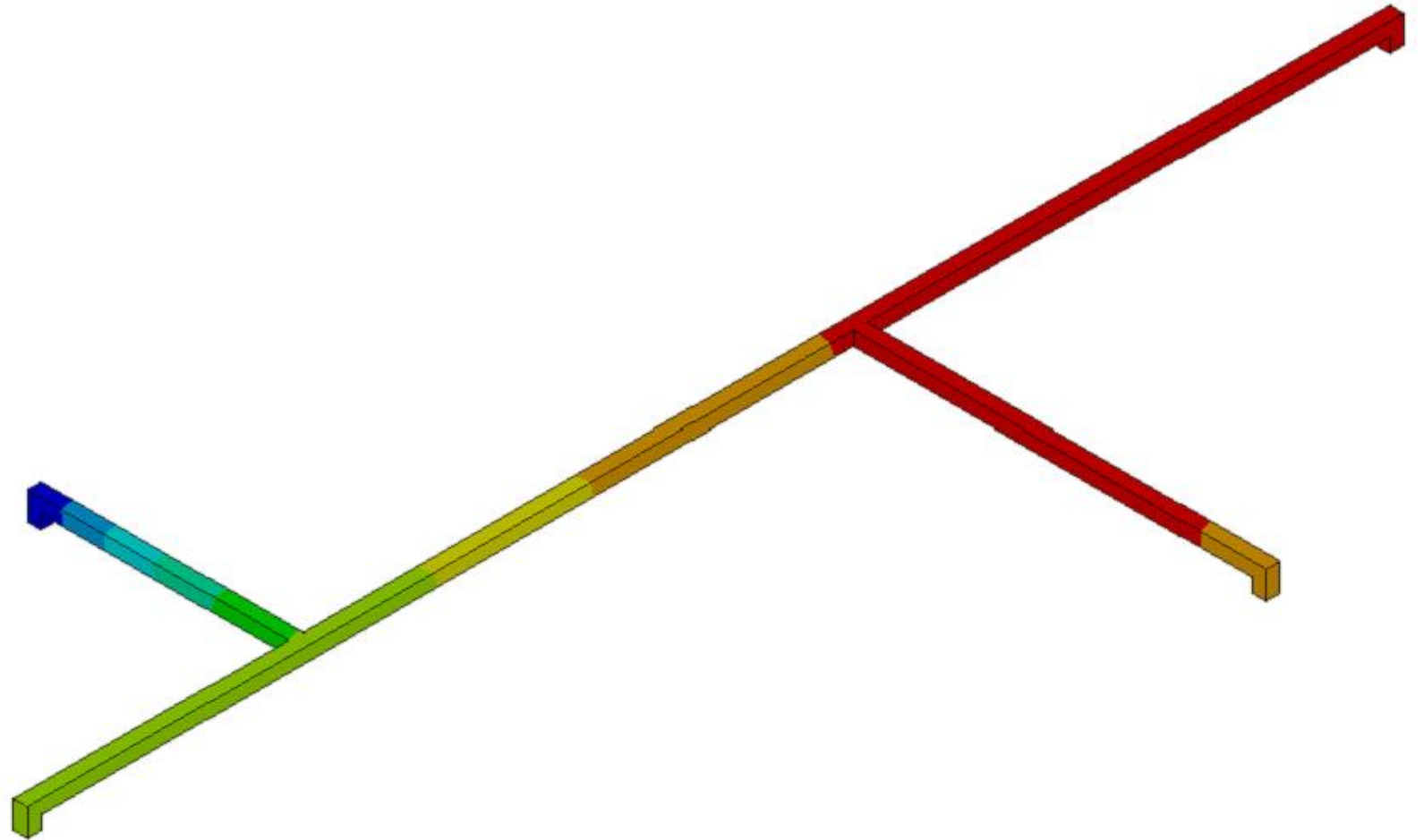
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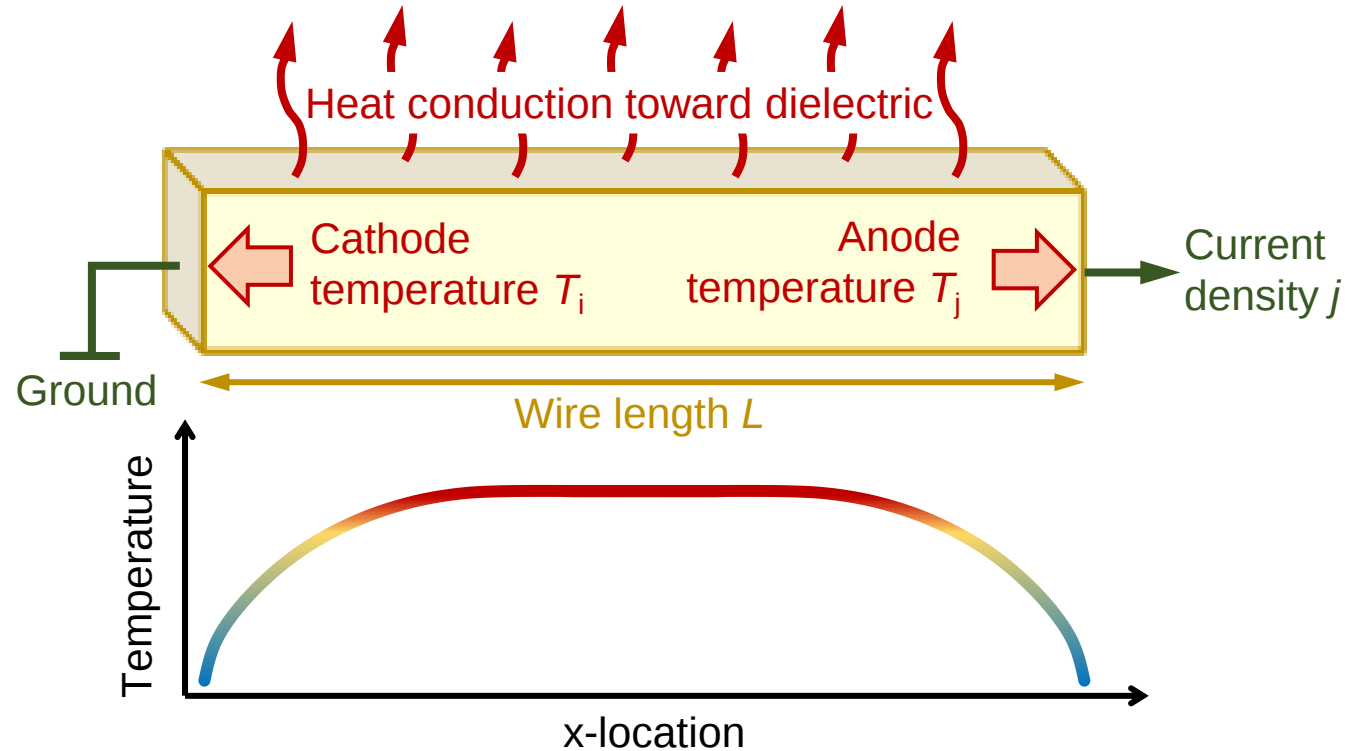
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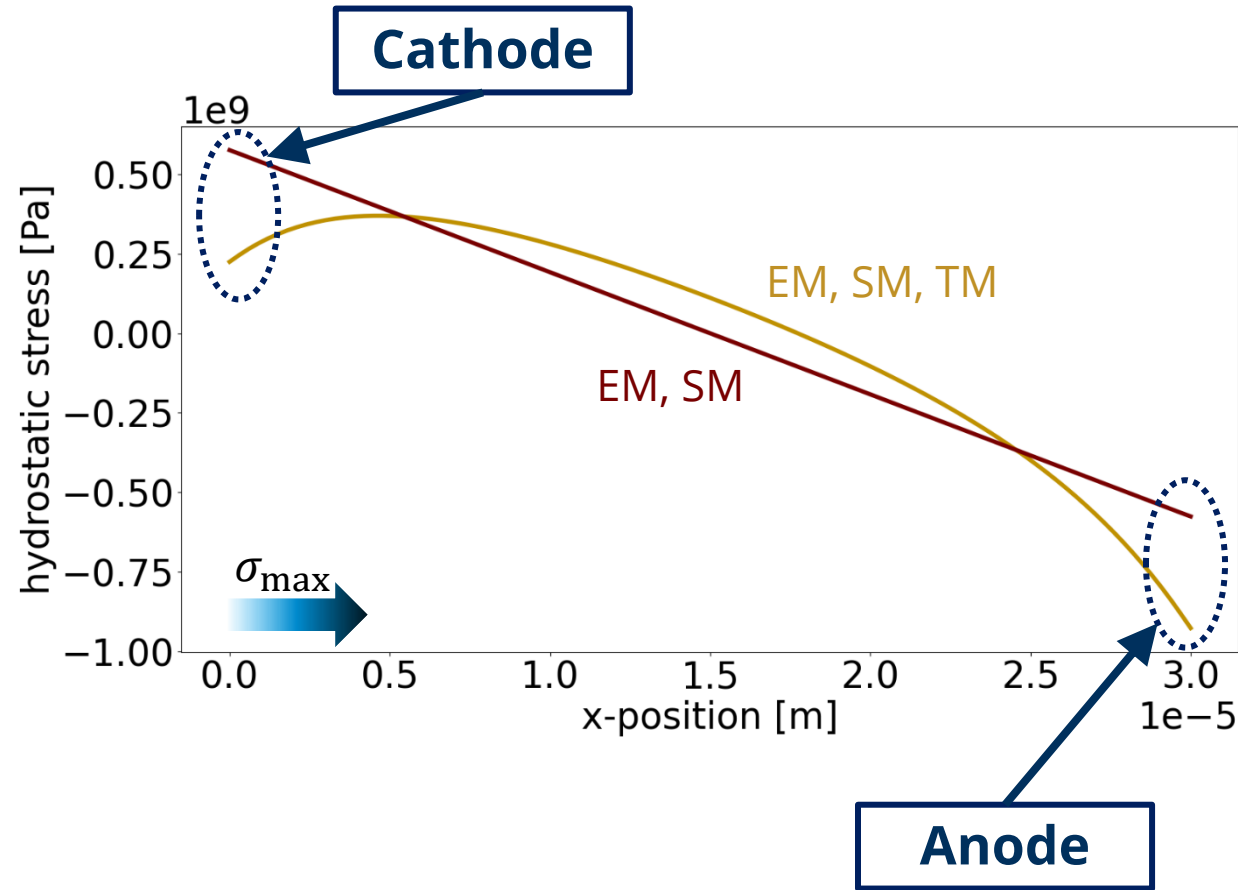


# FEM Models: General Concept



- Temperature rise is caused by Joule heating (no external heat sources)
- Self-healing is modeled by reducing the effective charge number  $Z$  in the diffusion equation of EM

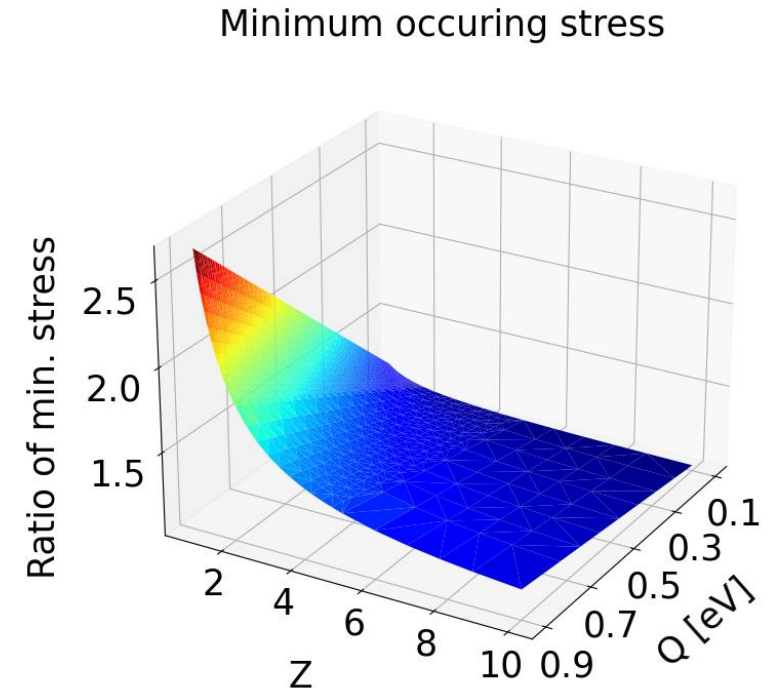
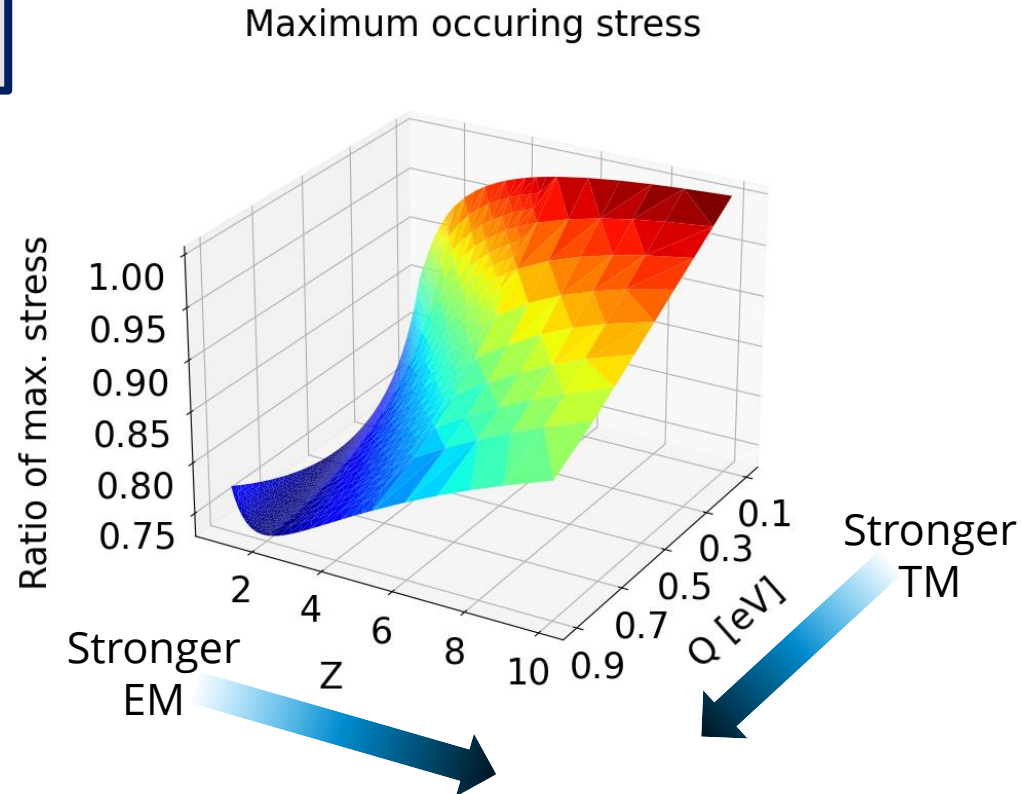
# FEM Models: Results



- TM consideration results in non-linear stress profile
- Cathode: reduced tensile stress
- Anode: increased compressive stress
- Stress maximum is not located at the cathode, but shifted toward the middle of the wire

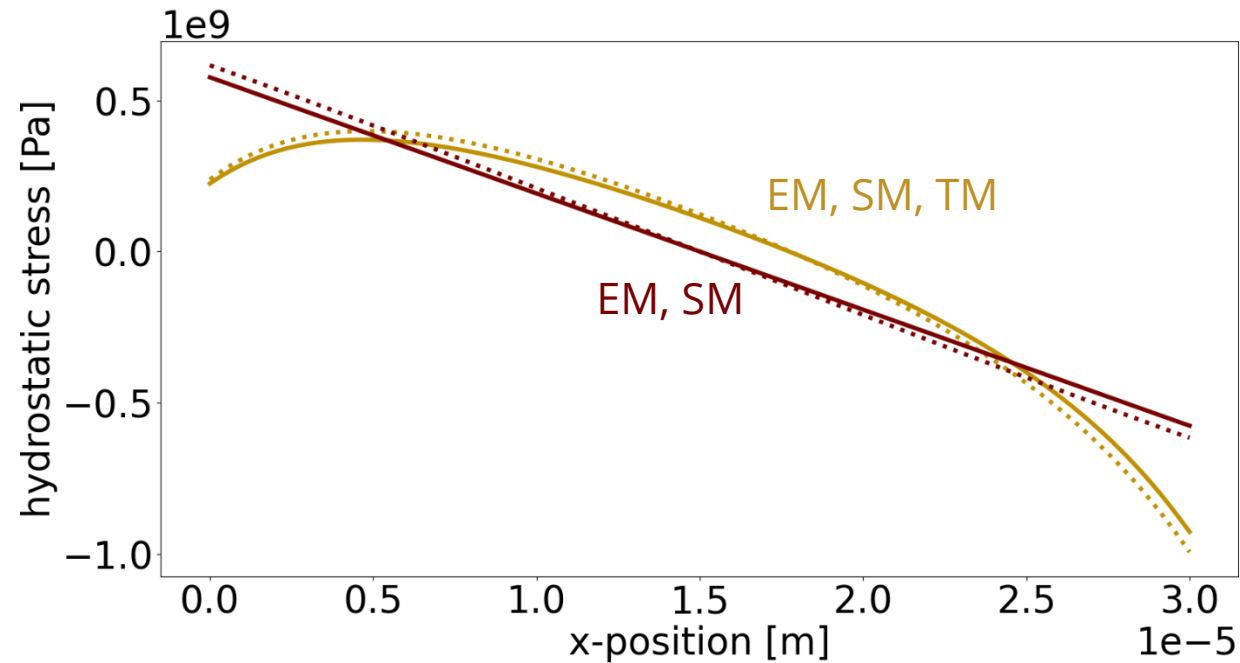
# FEM Models: Results

Ratio of  
TM/EM

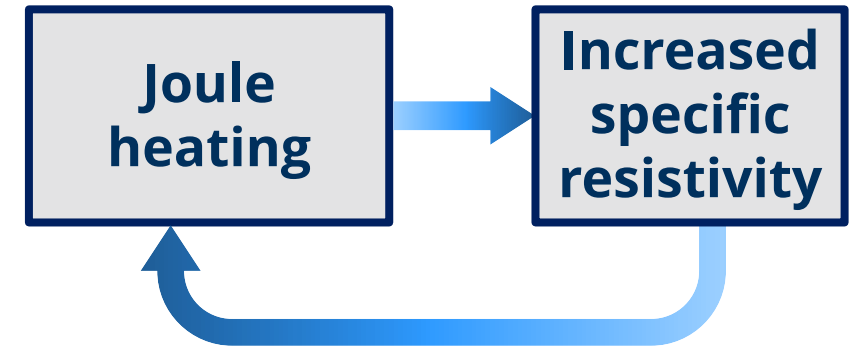


- Impact of TM varies depending on the values of Z (effective charge number) and Q (heat of transport)

# FEM Models: Results

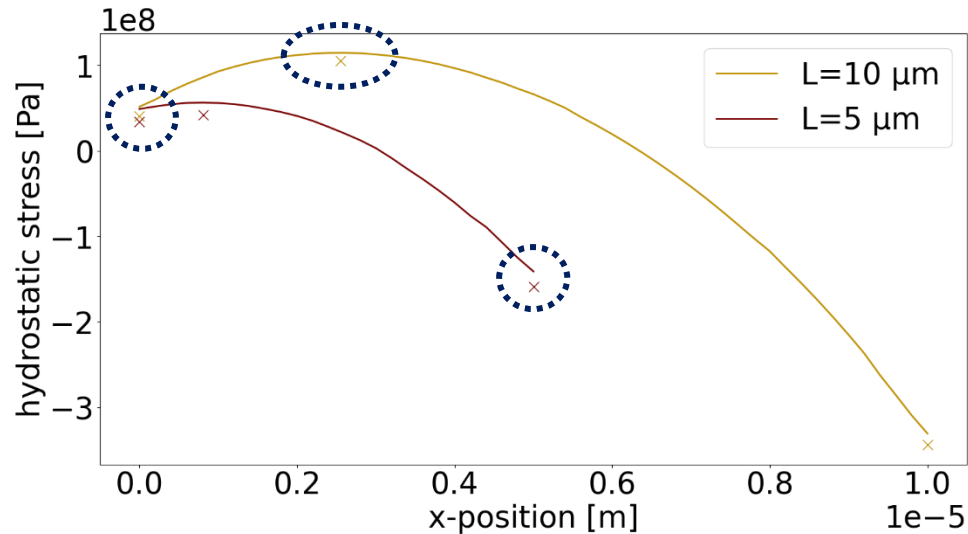
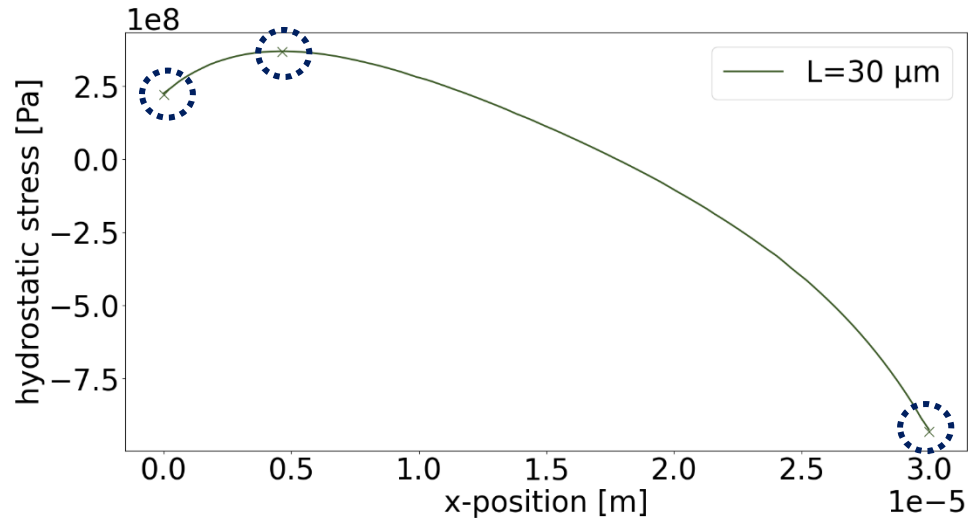


- Dotted lines: stress profile with consideration of temperature-dependent resistivity



- Impact is dependent from material parameters
- Always increases stress

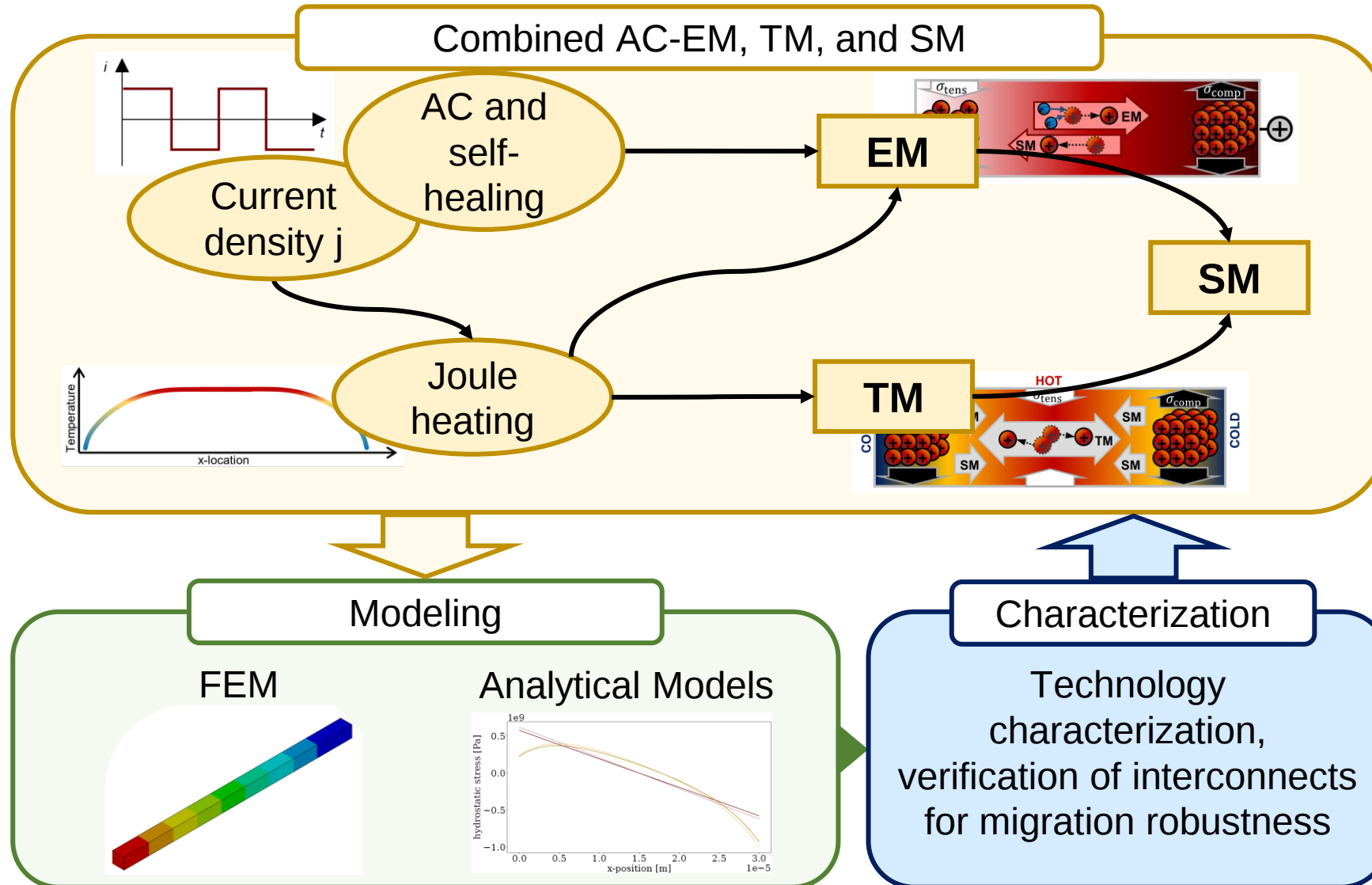
# FEM Models: Verification



Comparison with analytical models by Chen (2020)

- Good agreement for long wires
- Relative error gets bigger for shorter wires due to simplifications made in the analytical models
  - Tensile stress is underestimated
  - Compressive stress is overestimated
- New equation for location of stress maximum derived
  - Precise results for short wires (stress is still underestimated)

# FEM Models: Outlook



# FEM Models: Outlook

More precise modeling will require experimental validation

- FEM models can act as design guidelines
- Material parameters need to be specified by technology characterization
- Temperature profile of wires within a realistic chip context needs to be obtained

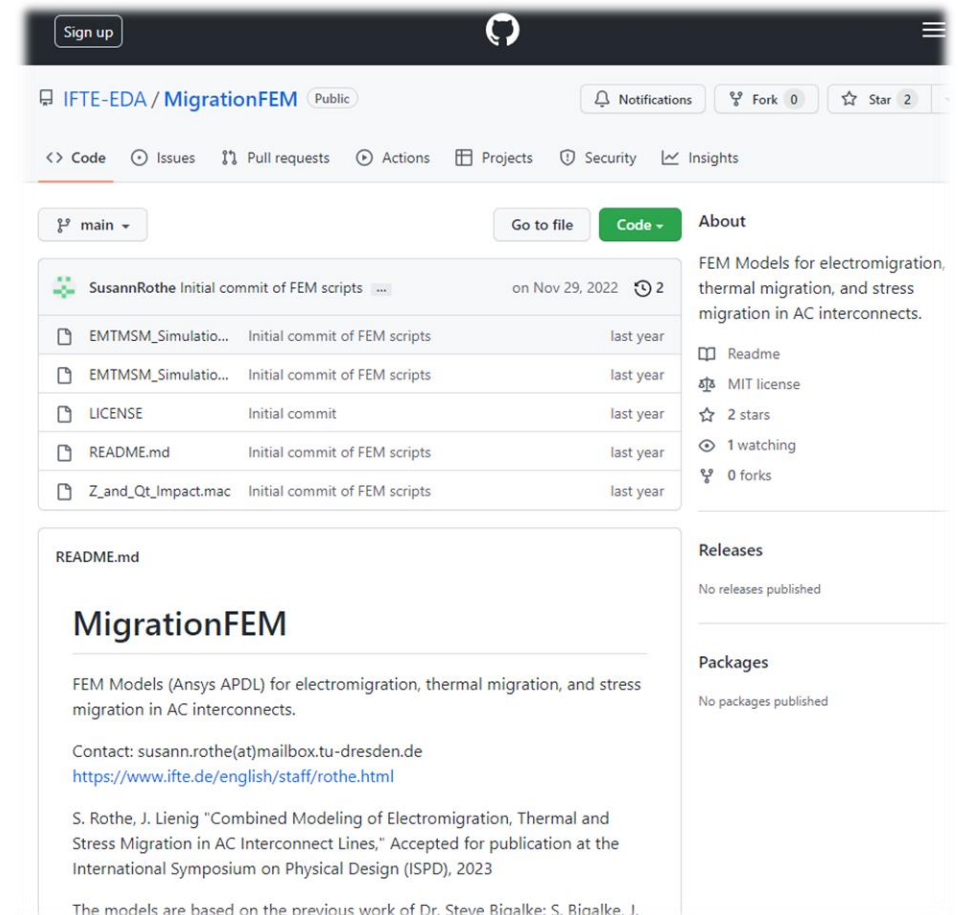
AC nets need to be designed in a migration-robust manner

- Full-chip FEM verification will be too time-consuming
- FEM models can be used to derive routing constraints and migration-inhibiting measures

# Summary

In this work, we developed:

- FEM models (Ansys® APDL) available on GitHub
  - Simulation of straight wires and more complex interconnect structures
  - Analysis of the impact of material parameters and temperature on AC-EM and TM
- An analytical model to
  - Find location of stress maximum
  - Calculate temperature along a wire considering temperature-dependent resistivity



<https://github.com/IFTE-EDA/MigrationFEM>

# Thank you for your attention!

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[www.ifte.de](http://www.ifte.de)

FEM models available on <https://github.com/IFTE-EDA/MigrationFEM>